

### FEATURES

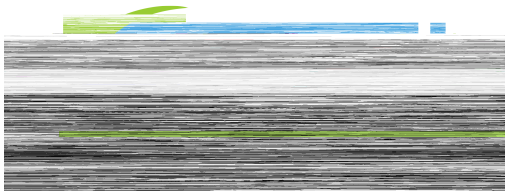
Fast Switching Speed  
 For General Purpose Switching Applications  
 High Conductance

#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	85	V
Continuous Reverse Voltage	$V_R$	75	V
Continuous Forward Current (Double Diode Loaded)	$I_F$	125	mA
Continuous Forward Current (Single Diode Loaded)	$I_F$	215	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	at $t = 1\text{ s}$ 0.5	A
		at $t = 1\text{ ms}$ 1	
		at $t = 1\text{ }\mu\text{s}$ 4.5	
Power Dissipation	$P_{tot}$	350	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	$V_F$	0.715	V
		0.855	
		1	
		1.25	
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_j = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}, T_j = 150\text{ }^\circ\text{C}$	$I_R$	30	nA
		1	$\mu\text{A}$
		30	$\mu\text{A}$
		50	$\mu\text{A}$
Diode Capacitance at $V_R = 0$ , $f = 1\text{ MHz}$	$C_d$	1.5	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$ , $I_R = 1\text{ mA}$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	4	ns



### Typical Characteristics

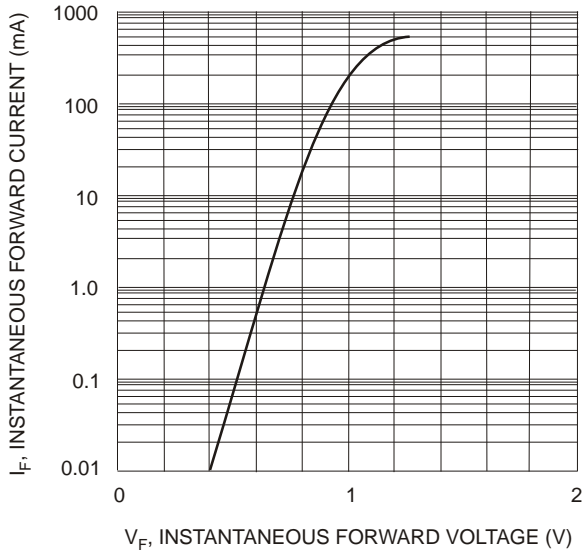


Fig. 1 Forward Characteristics

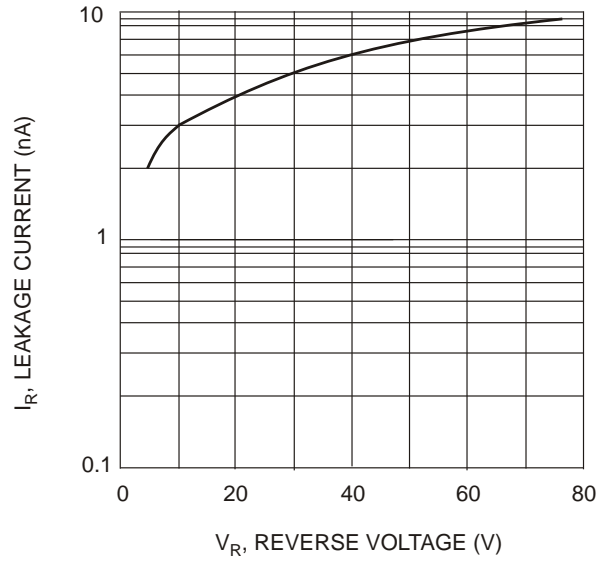


Fig. 2 Typical Leakage Current vs Reverse Voltage

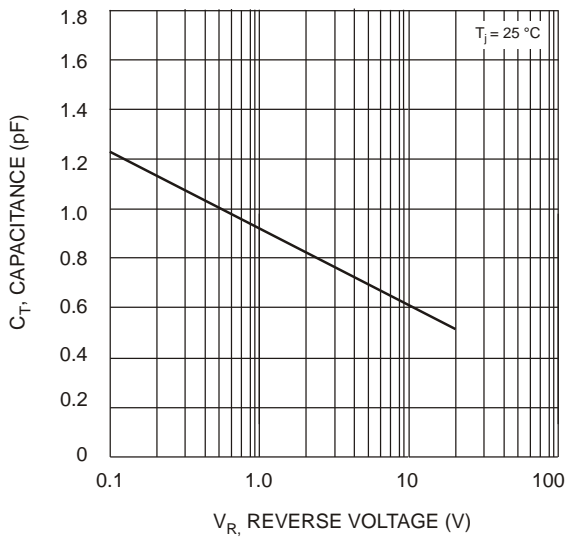


Fig. 3 Typical Total Capacitance vs Reverse Voltage



# BAV99

## Si ching Diode

### PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

